

EMX2DXV6T5

Preferred Devices

Dual NPN General Purpose Amplifier Transistor

This NPN transistor is designed for general purpose amplifier applications. This device is housed in the SOT-563 package which is designed for low power surface mount applications, where board space is at a premium.

Features

- Reduces Board Space
- High h_{FE} , 210–460 (Typical)
- Low $V_{CE(sat)}$, < 0.5 V
- These are Pb-Free Devices

MAXIMUM RATINGS ($T_A = 25^\circ\text{C}$)

Rating	Symbol	Value	Unit
Collector-Base Voltage	$V_{(BR)CBO}$	60	Vdc
Collector-Emitter Voltage	$V_{(BR)CEO}$	50	Vdc
Emitter-Base Voltage	$V_{(BR)EBO}$	7.0	Vdc
Collector Current – Continuous	I_C	100	mAdc

THERMAL CHARACTERISTICS

Characteristic (One Junction Heated)	Symbol	Max	Unit
Total Device Dissipation $T_A = 25^\circ\text{C}$ Derate above 25°C	P_D	357 (Note 1) 2.9 (Note 1)	mW mW/ $^\circ\text{C}$
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	350 (Note 1)	$^\circ\text{C/W}$
Characteristic (Both Junctions Heated)	Symbol	Max	Unit
Total Device Dissipation $T_A = 25^\circ\text{C}$ Derate above 25°C	P_D	500 (Note 1) 4.0 (Note 1)	mW mW/ $^\circ\text{C}$
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	250 (Note 1)	$^\circ\text{C/W}$
Junction and Storage Temperature Range	T_J, T_{stg}	–55 to +150	$^\circ\text{C}$

Maximum ratings are those values beyond which device damage can occur. Maximum ratings applied to the device are individual stress limit values (not normal operating conditions) and are not valid simultaneously. If these limits are exceeded, device functional operation is not implied, damage may occur and reliability may be affected.

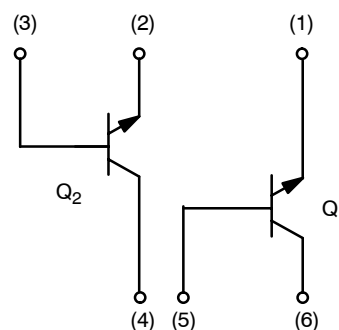
1. FR–4 @ Minimum Pad



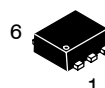
ON Semiconductor®

<http://onsemi.com>

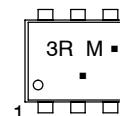
DUAL NPN GENERAL PURPOSE AMPLIFIER TRANSISTORS SURFACE MOUNT



MARKING DIAGRAM



SOT-563
CASE 463A
STYLE 2



3R = Specific Device Code

M = Month Code

■ = Pb-Free Package

(Note: Microdot may be in either location)

ORDERING INFORMATION

Device	Package	Shipping†
EMX2DXV6T5	SOT-563 (Pb-Free)	8000/Tape & Reel
EMX2DXV6T5G	SOT-563 (Pb-Free)	8000/Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

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ELECTRICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$)

Characteristic	Symbol	Min	Typ	Max	Unit
Collector-Base Breakdown Voltage ($I_C = 50\ \mu\text{Adc}$, $I_E = 0$)	$V_{(BR)CBO}$	60	–	–	Vdc
Collector-Emitter Breakdown Voltage ($I_C = 1.0\ \text{mAdc}$, $I_B = 0$)	$V_{(BR)CEO}$	50	–	–	Vdc
Emitter-Base Breakdown Voltage ($I_E = 50\ \mu\text{Adc}$, $I_C = 0$)	$V_{(BR)EBO}$	7.0	–	–	Vdc
Collector-Base Cutoff Current ($V_{CB} = 60\ \text{Vdc}$, $I_E = 0$)	I_{CBO}	–	–	0.5	μA
Emitter-Base Cutoff Current ($V_{EB} = 7.0\ \text{Vdc}$, $I_B = 0$)	I_{EBO}	–	–	0.5	μA
Collector-Emitter Saturation Voltage (Note 2) ($I_C = 50\ \text{mAdc}$, $I_B = 5.0\ \text{mAdc}$)	$V_{CE(sat)}$	–	–	0.4	Vdc
DC Current Gain (Note 3) ($V_{CE} = 6.0\ \text{Vdc}$, $I_C = 1.0\ \text{mAdc}$)	h_{FE}	120	–	560	–
Transition Frequency ($V_{CE} = 12\ \text{Vdc}$, $I_C = 2.0\ \text{mAdc}$, $f = 30\ \text{MHz}$)	f_T	–	180	–	MHz
Output Capacitance ($V_{CB} = 12\ \text{Vdc}$, $I_C = 0\ \text{Adc}$, $f = 1\ \text{MHz}$)	C_{OB}	–	2.0	–	pF

2. Device mounted on a FR-4 glass epoxy printed circuit board using the minimum recommended footprint.
3. Pulse Test: Pulse Width $\leq 300\ \mu\text{s}$, D.C. $\leq 2\%$.

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TYPICAL ELECTRICAL CHARACTERISTICS

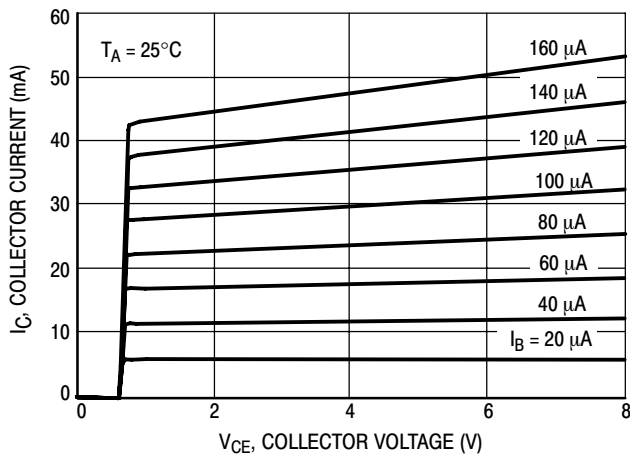


Figure 1. $I_C - V_{CE}$

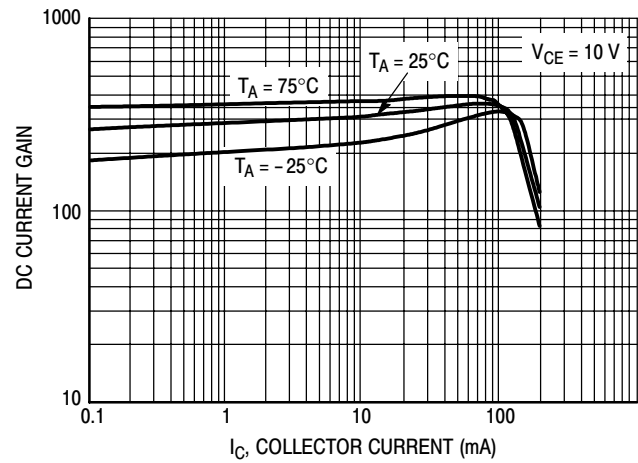


Figure 2. DC Current Gain

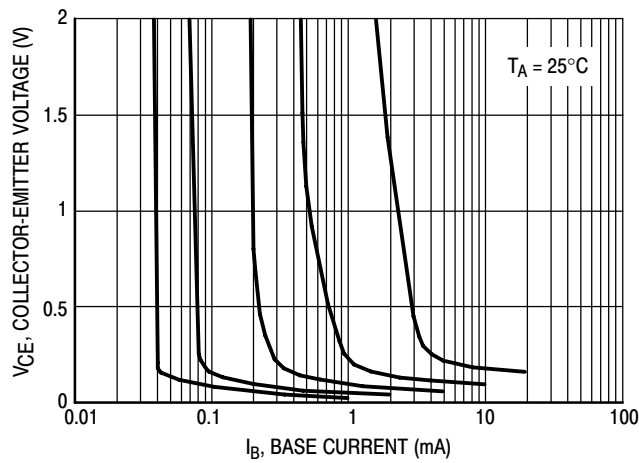


Figure 3. Collector Saturation Region

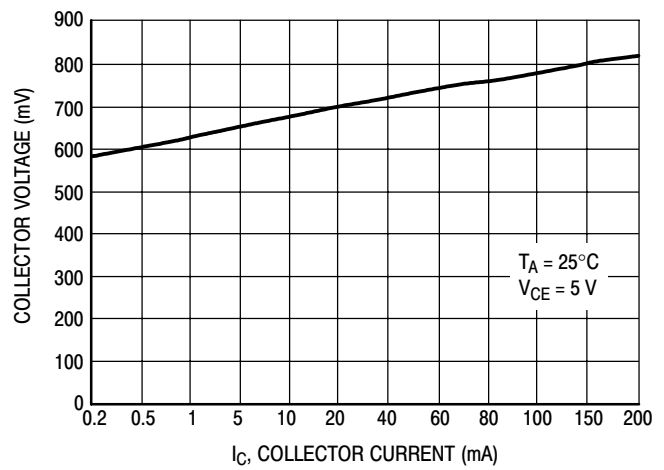


Figure 4. On Voltage

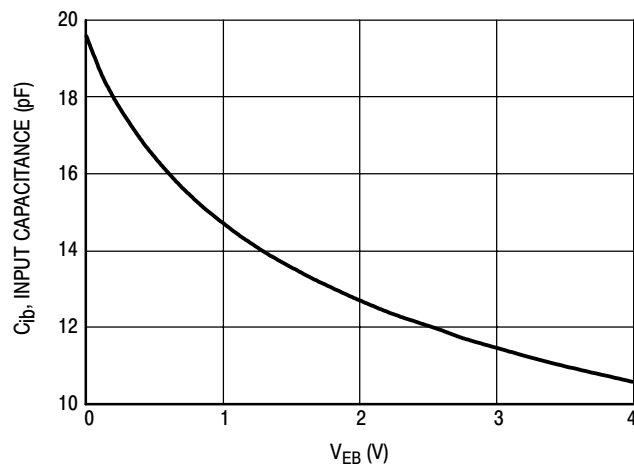


Figure 5. Capacitance

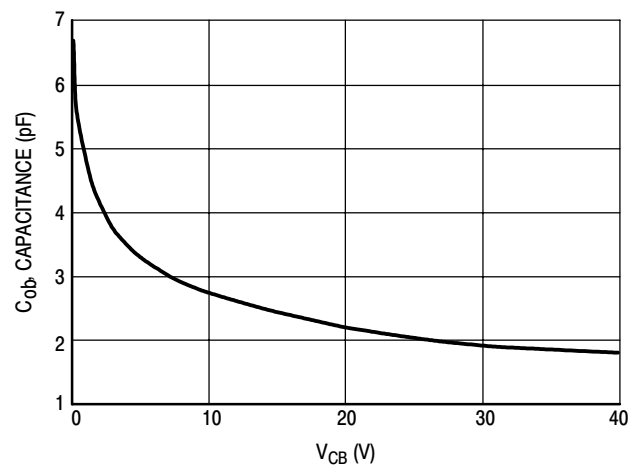


Figure 6. Capacitance

